



1.0A/1.5A/2.0A SINGLE CHANNEL POWER DISTRIBUTION LOAD SWITCH

Description

The DIODES™ AP22816/17/18 is a single-channel, current-limited, integrated high-side power switch optimized for Universal Serial Bus (USB) and other hot-swap applications. The family of devices complies with USB standards and is available with both polarities of enable input.

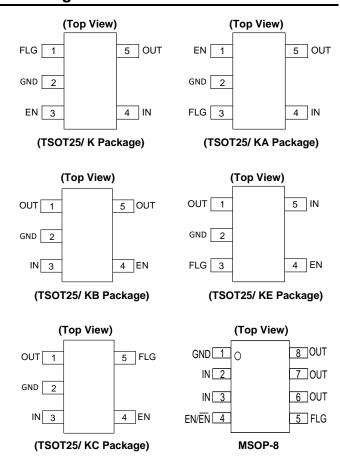
The device has fast short-circuit response time for improved overall system robustness, and has an integrated output discharge function to ensure completely controlled discharging of the output voltage capacitor. They provide a complete protection solution for applications subject to heavy capacitive loads and the prospect of short circuit, and offer reverse current blocking, overcurrent, overtemperature and short-circuit protection, as well as controlled rise time and undervoltage lockout functionality. A 6ms deglitch capability on the open-drain flag output prevents false overcurrent reporting and does not require any external components.

The AP22816/17/18 is available in the standard Green and RoHS compliant TSOT25 and MSOP-8 packages.

Features

- Input Voltage Range: 2.7V to 5.5V
- 75mΩ On-resistance
- Built-in Soft-start with 0.6ms Typical Rise Time
- Fault Report (FLG) with Blanking Time (6ms Typ.)
- ESD Protection: 2kV HBM, 500V CDM
- Logic Level Enable Pin: Available with Active-high or Active-low Versions
- Protections:
 - Overcurrent Protection with Auto Recovery
 - Short-Circuit Protection with Auto Recovery
 - Overtemperature Protection with Auto Recovery
 - Output Reverse Current / Voltage Protection
- Thermally-Efficient Low Profile Package
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals:
 - TSOT-25: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (e3)
 - MSOP-8: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (e3)
- Weight:
 - TSOT25: 0.013 grams (Approximate)
 - MSOP-8: 0.027grams(Approximate)
- UL Recognized, File Number E322375
- IEC60950-1 CB Scheme Certified
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Pin Assignments



Applications

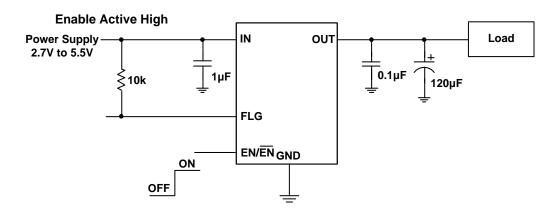
- Integrated load switches in Ultrabook PCs
- Power up/down sequencing in Ultrabook PCs
- Notebooks
- Netbooks
- Set-top boxes
- SSD (solid state drives)
- Consumer electronics
- Tablet PCs
- Telecom systems

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Typical Applications Circuit



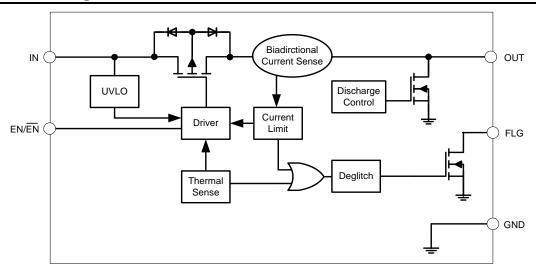
Note: If $1\mu F$ input cap. Will lead to large V_{IN} spike, it's recommended to use $10\mu F$ capacitor instead.

Pin Descriptions

Pin N	Pin Number		Fundian
TSOT25	MSOP-8	- Pin Name	Function
5(K/KA)			VII. 0 - 15 - 1 - 1 - 1 - 1 - 1
1, 5(KB)	6, 7, 8	OUT	Voltage Output Pin, connect a 0.1µF bypass capacitor and a high-value capacitor to GND, close to IC. (At least 10µF in USB applications.)
1(KE)			departer to GND, close to 10. (At least 10th in GGD applications.)
2	1	GND	Ground pin of the circuitry
1(K)			Outstand Outstand Outstand for Hannel
3(KA/KE)	5	FLG	Overcurrent and Overtemperature fault report; Open-Drain flag is active-low when triggered.
5(KC)			Open-Drain hag is active-low when triggered.
3(K)			Enable input
1(KA)	4	EN/EN	AP22816A/17A/18A: Active-High
4(KB/KE)	7		AP22816B/17B/18B: Active-Low
4(K/KA)			
3(KB)	2, 3	IN	Voltage Input Pin, connect a 1µF low ESR capacitor to GND, close to IC.
5(KE)			



Functional Block Diagram



Absolute Maximum Ratings (@ TA = +25°C, unless otherwise specified.) (Note 4)

Syr	nbol	Parameter		Ratings	Units
	HBM	luman Body ESD Protection		2000	V
ESD	CDM	Charged Device Model ESD Protection		500	V
LOD	IEC System Level	Surges per IEC61000-4-2. 1999 Applied to Output Terminals of EVM (Note 6)		15	kV
\	'IN	Input Voltage		-0.3 to 6.0	V
V	V _{OUT} Output Voltage		-0.3 to (V _{IN} +0.3)	V	
VE	V _{EN/EN} Enable Voltage		Enable Voltage		V
	I _L	Load Current		Internal Limited	°C
TJ	T _{J(max)} Maximum Junction Temperature		+150	°C	
Т	T _{ST} Storage Temperature		-65 to +150	°C	
		Thermal Resistance, Junction to Ambient	MSOP-8 (Note 5, 7)	165	
R	$R_{\theta JA}$	Thermal Resistance, Junction to Case	TSOT25 (Note 6, 7)	123	°C/W
В		The second Desistance Associates to Con-	MSOP-8 (Note 5, 7)	33	C/VV
R _{0JC}		Thermal Resistance, Junction to Case	TSOT25 (Note 6, 7)	32	

Notes:

- 4. Stresses greater than the 'Absolute Maximum Ratings' specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.
- 5. External capacitors need to be connected to the output, EVM board was tested with external capacitor. This level is a pass test only and not a limit
- 6. Test condition for TSOT25/MSOP-8: Device mounted on 1"x1"/2"x2" FR-4 substrate PC board, 2oz copper with minimum recommended pad layout.
- 7. R0JA and R0JC are measured at T_A = 25°C on a high effective thermal conductivity four-layer test board per JEDEC 51-7.

Recommended Operating Conditions (@ T_A = +25°C, unless otherwise specified.) (Note 8)

Symbol		Parameter		Max	Unit
V _{IN}	Input Voltage	Input Voltage		5.5	V
		AP22816	0	1.0	
lout	Output Current	AP22817	0	1.5	А
		AP22818	0	2.0	
VIL	EN/EN Input Logic L	EN/EN Input Logic Low Voltage		0.5	V
VIH	EN/EN Input Logic High Voltage		1.5	V _{IN}	V
TA	Operating Ambient 7	emperature	-40	+85	°C

Note: 8. Refer to the typical application circuit.



Electrical Characteristics ($V_{IN} = 5V @ T_A = +25^{\circ}C$, $C_{IN} = 1\mu F$, $C_L = 100nF$, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _U VLO	Input UVLO	V _{IN} Rising	1.8	2.3	2.6	V
ΔV_{UVLO}	Input UVLO Hysteresis	V _{IN} Decreasing	_	180	_	mV
I _{SHDN}	Input Shutdown Current	Disabled, OUT = Open	_	0.1	1	μΑ
ΙQ	Input Quiescent Current	Enabled, OUT = Open	_	80	_	μΑ
I _{LEAK}	Input Leakage Current	Disabled, OUT Grounded	_	0.1	1	μΑ
I _{REV}	Reverse Leakage Current	Disabled, V _{IN} = 0V, V _{OUT} = 5V, I _{REV} at V _{IN}	_	0.01	1	μΑ
R _{DS(ON)}	Switch On-Resistance	$V_{IN} = 5V, I_{OUT} = 1A$ $T_A = +25^{\circ}C$	_	75	95	mΩ
		V _{IN} = 5V, V _{OUT} = 4.5V(AP22818)	2.2	2.7	3.2	Α
I _{LIMIT}	Over Load Current Limit	V _{IN} = 5V, V _{OUT} = 4.5V(AP22817)	1.65	2.2	2.8	Α
		V _{IN} = 5V, V _{OUT} = 4.5V(AP22816)	1.1	1.5	2.1	Α
I _{SHORT}	Short-Circuit Current Limit	Enabled, Output short to ground	_	0.5	_	Α
V _{IL}	EN/EN Input Logic Low Voltage	V _{IN} = 2.7V to 5.5V	_	_	0.5	V
V _{IH}	EN/EN Input Logic High Voltage	V _{IN} = 2.7V to 5.5V	1.5	_	_	V
I _{LEAK-EN/EN}	EN/EN Input Leakage	$V_{IN} = 5V$, $V_{EN/\overline{EN}} = 0V$ and 5.5V	_	0.01	1	μΑ
I _{LEAK-O}	Output Leakage Current	Disabled, V _{OUT} = 0V	_	0.5	1	μΑ
t _{D(ON)}	Output Turn-On Delay Time	$C_L = 4.7 \mu F$, $R_{LOAD} = 10 \Omega$ @ $V_{IN} = 3.3 V$ Figure 1	_	1.5	_	ms
t _R	Output Turn-On Rise Time	$C_L = 4.7 \mu F$, $R_{LOAD} = 10 \Omega$ @ $V_{IN} = 3.3 V$ Figure 1	1.0	2.1	3.5	ms
t _{D(OFF)}	Output Turn-Off Delay Time	$C_L = 4.7 \mu F$, $R_{LOAD} = 10 \Omega$ @ $V_{IN} = 3.3 V$ Figure 1	_	20	_	μs
t _F	Output Turn-Off Fall Time	$C_L = 4.7 \mu F$, $R_{LOAD} = 10 \Omega$ @ $V_{IN} = 3.3 V$ Figure 1	_	0.15	_	ms
R _{FLG}	FLG Output FET On-Resistance	I _{FLG} = 10mA	_	30	60	Ω
I _{FOH}	FLG Off Current	V _{FLG} = 5V	_	0.01	1	μA
t _{BLANK}	FLG Blanking Time	Assertion or deassertion due to overcurrent and overtemperature condition	2	5	15	ms
t _{DIS}	Discharge Time	$C_L = 1\mu F$, $V_{IN} = 5V$, disabled to $V_{OUT} < 0.5V$	_	0.4	_	ms
R _{DIS}	Discharge Resistance	V _{IN} = 5V, Disabled, I _{OUT} = 1mA	_	140	200	Ω
T _{SHDN}	Thermal Shutdown Threshold	Enabled	_	+150	_	°C
T _{HYS}	Thermal Shutdown Hysteresis	_	_	+40	_	°C
V _{RVP}	Reverse-Voltage Comparator Trip Point	V _{OUT} - V _{IN}	35	70	105	mV
I _{ROCP}	Reverse Current Limit	V _{OUT} - V _{IN} = 150mV	_	350	_	mA
t _{TRIG}	Time from Reverse-Voltage Condition to MOSFET Turn off	Vin	2	5	15	ms

Performance Characteristics

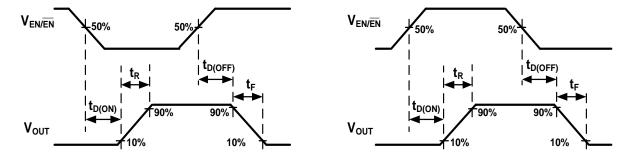
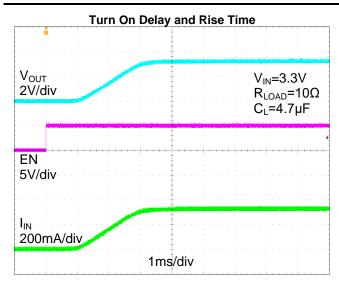
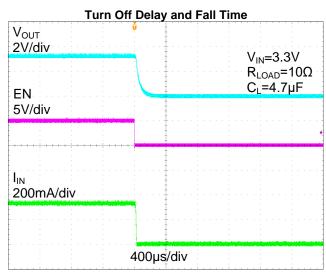


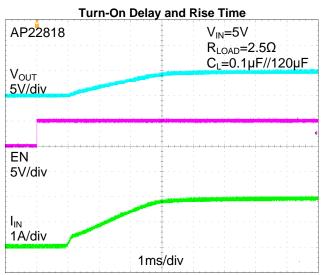
Figure 1. Voltage Waveforms: AP22816B (Active Low, Left), AP22816A (Active High, Right)

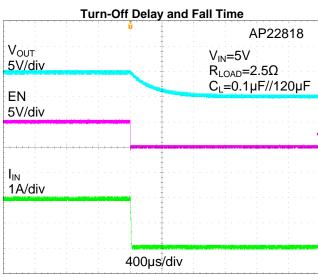


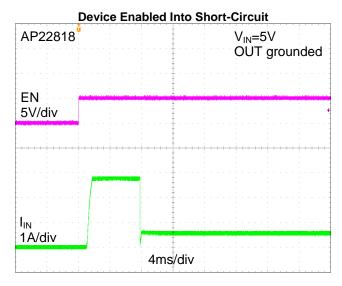
$\label{eq:performance Characteristics} \textbf{ ($T_A = +25^{\circ}$C, $V_{IN} = 5$V, $C_{IN} = 1$\mu$F, $C_L = 0.1$\mu$F, unless otherwise specified.) (continued)}$

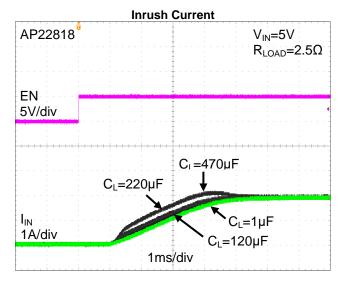






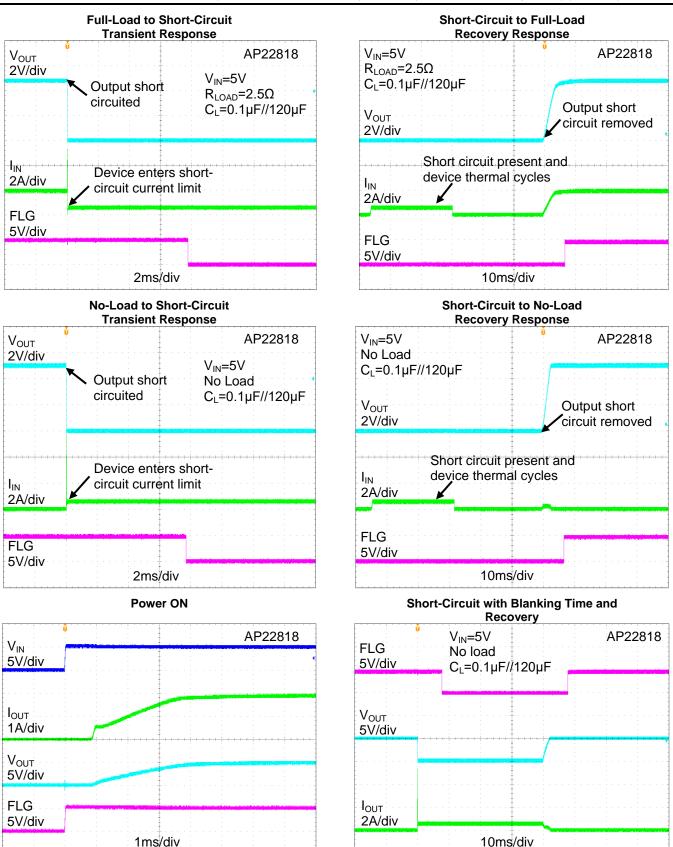






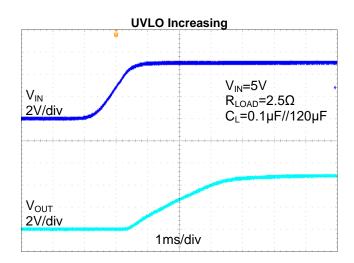


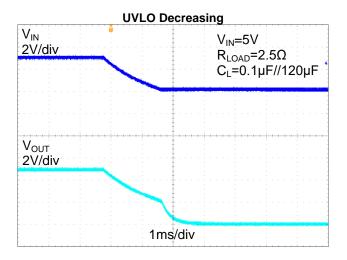
$\label{eq:performance Characteristics} \textbf{(} T_{A} = +25^{\circ}\text{C}, \textbf{V}_{IN} = 5\text{V}, \textbf{C}_{IN} = 1\mu\text{F}, \textbf{C}_{L} = 0.1\mu\text{F}, \textbf{unless otherwise specified.)} \textbf{(} \textbf{continued)}$

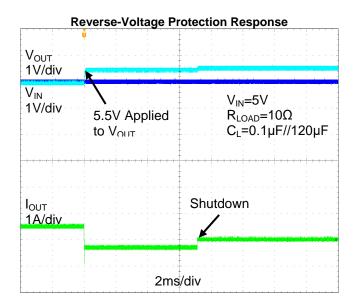


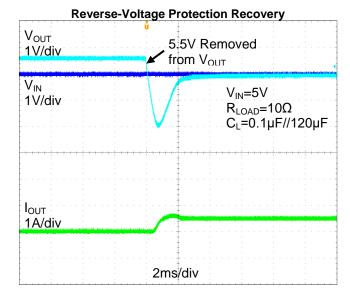


$\label{eq:performance Characteristics} \textbf{(}T_{A} = +25^{\circ}\text{C, } V_{IN} = 5\text{V, } C_{IN} = 1\mu\text{F, } C_{L} = 0.1\mu\text{F, unless otherwise specified.)} \textbf{(}continued)$



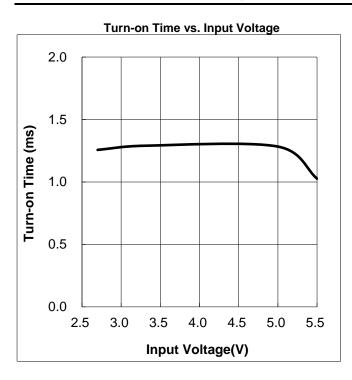


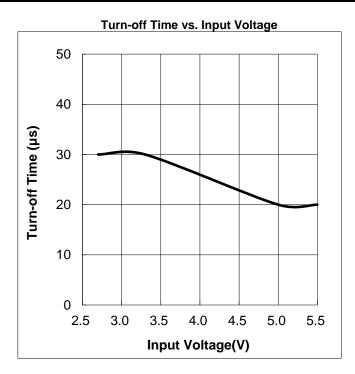


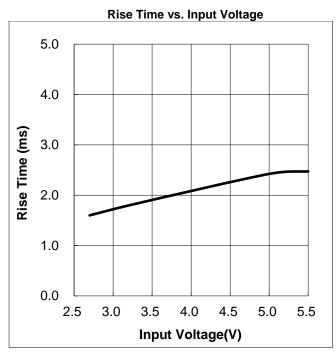


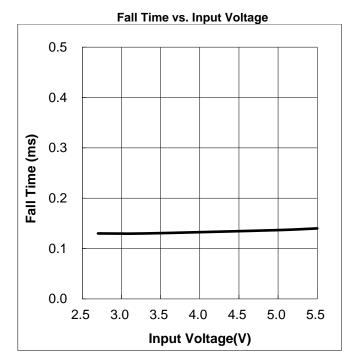


$\hline \textbf{Performance Characteristics} \ (T_A = +25^{\circ}\underline{C}, \ V_{IN} = 5V, \ C_{IN} = 1\mu\text{F}, \ C_L = 0.1\mu\text{F}, \ unless otherwise specified.}) \ (continued)$



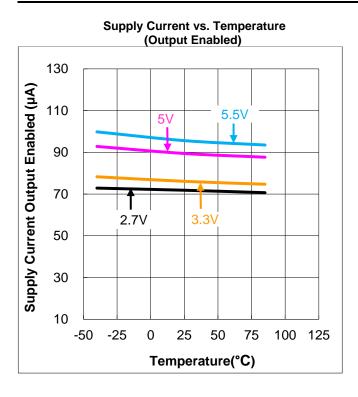


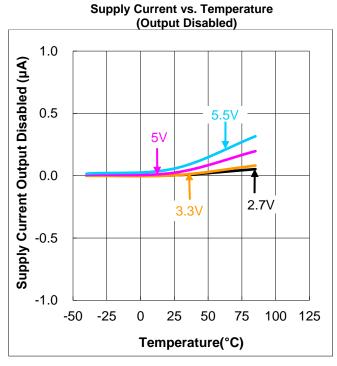


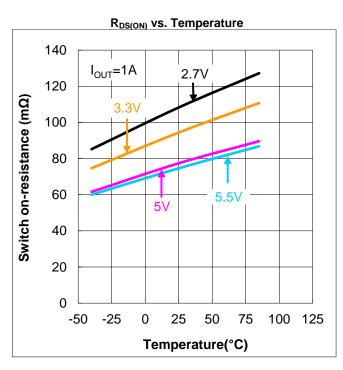


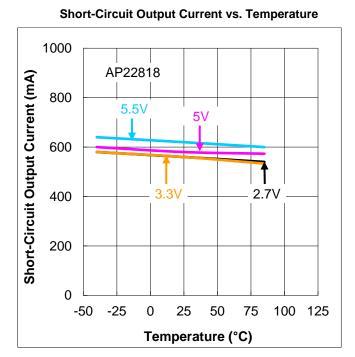


$\textbf{Performance Characteristics} \text{ ($T_A = +25^{\circ}$C, $V_{IN} = 5$V, $C_{IN} = 1$\mu$F, $C_L = 0.1$\mu$F, unless otherwise specified.) (continued) }$



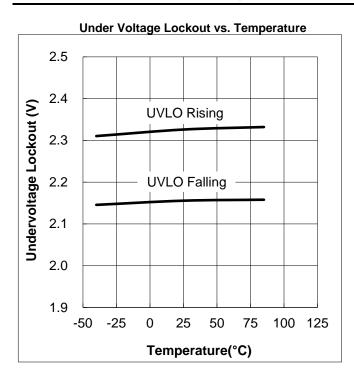


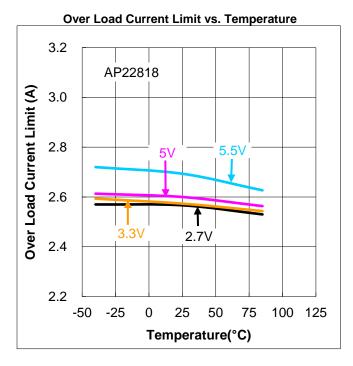




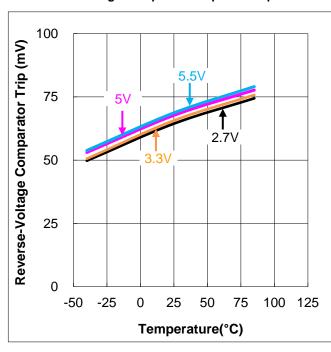


Performance Characteristics ($T_A = +25$ °C, $V_{IN} = 5$ V, $C_{IN} = 1\mu$ F, $C_L = 0.1\mu$ F, unless otherwise specified.) (continued)

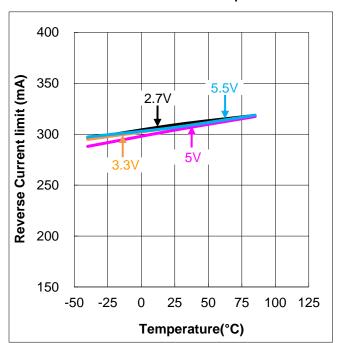




Reverse-Voltage Comparator Trip vs. Temperature



Reverse Current Limit vs. Temperature





Application Information

Input and Output Capacitors

It is needed to place a $1\mu F$ X7R or X5R ceramic bypass capacitor between the IN and GND, close to the device. Placing a high-value capacitor ($10\mu F$ or $47\mu F$) close to the input pin is also recommended when the output transient load is heavy. This precaution reduces power-supply transients that may cause ringing on the input.

Also needed for hot-plug applications is the connection of a minimum 100µF low ESR electrolytic or tantalum capacitor (or 10µF MLCC) between OUT and GND is. It is necessary to bypass the output with a 0.1µF ceramic capacitor, which improves the immunity of the device to short-circuit transients. The Bulky 100µF or larger capacitors help to reduce output droop voltage when a device is plugged in. When abnormal short-circuit condition happens, these capacitors can also reduce output negative voltage due to parasitic inductive effect and avoid device damage.

Please note that without the bypass capacitors, an output short may cause ringing on the input; if the voltage is over the maximum voltage rating, it will destroy the internal control circuitry even if the duration is short.

FLG Response

When an overcurrent or overtemperature shutdown condition is encountered, the FLG open-drain output goes active low after a nominal 6ms deglitch timeout. The FLG output remains low until both overcurrent and overtemperature conditions are removed. Connecting a heavy capacitive load to the output of the device can cause a momentary overcurrent condition, which does not trigger the FLG due to the 6ms deglitch timeout. The AP22816(1.0A)/17(1.5A)/18(2.0A) is designed to eliminate false overcurrent reporting without the need of external components to remove unwanted pulses.

Overcurrent and Short Circuit Protection

An internal sensing FET is employed to check for overcurrent conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted to GND before the device is enabled or before V_{IN} has been applied. The AP22816(1.0A)/17(1.5A)/18(2.0A) senses the short circuit and immediately clamps output current to a certain safe level.

In the second condition, an output short or an overload occurs while the device is enabled. At the instance the overload occurs, higher current may flow for a very short period of time before the current limit function can react. After the current limit function has tripped, the device switches into current limiting mode and the current is clamped at I_{LIMIT}, or I_{SHORT}.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold (I_{TRIG}) is reached or until the thermal limit of the device is exceeded. The AP22816(1.0A)/17(1.5A)/18(2.0A) is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its current limiting mode and is set at I_{LIMIT}.

Thermal Protection

Thermal protection prevents the IC from damage when heavy-overload or short-circuit faults are present for extended periods of time. The AP22816(1.0A)/17(1.5A)/18(2.0A) implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately +140°C due to excessive power dissipation in an overcurrent or short-circuit condition, the internal thermal sense circuitry turns the power switch off, thus preventing the power switch from damage. Hysteresis is built into the thermal sense circuit allowing the device to cool down approximately +35°C before the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed. The FLG open-drain output is asserted when an overtemperature shutdown or overcurrent occurs with 6ms deglitch.

ON/OFF Input Operator

The EN/EN input allows the output current to be switched on and off using a GPIO compatible input. The high signal (switched on) should be at least 1.5V, and the low signal (switch off) no higher than 0.65V. This pin should not be left floating. It is advisable to hold the EN/EN signal low when applying or removing power.



Application Information (continued)

Undervoltage Lockout (UVLO)

Undervoltage lockout function (UVLO) keeps the internal power switch from being turned on until the power supply has reached at least 2V, even if the switch is enabled. Whenever the input voltage falls below approximately 2V, the power switch is quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.

Discharge Function

The discharge function of the device is active when the enable is disabled or de-asserted. The discharge function with the N-MOS power switch implementation is activated and offers a resistive discharge path for the external storage capacitor. This is designed for discharging any residue of the output voltage when either no external output resistance or load resistance is present at the output.

Output Reverse-Voltage/Current Protection

The output reverse-voltage protection turns off the MOSFET switch whenever the output voltage is higher than the input voltage by 50mV for 6ms. The MOSFET switch will turn on when output reverse-voltage/current conditions are removed.

Power Dissipation and Junction Temperature

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large currents. Using the maximum operating ambient temperature (T_A) and R_{DS(ON)}, the power dissipation can be calculated by:

 $P_D = R_{DS(ON)} \times I^2$

Finally, calculate the junction temperature:

 $T_J = P_D \times R_{\theta JA} + T_A$

Where:

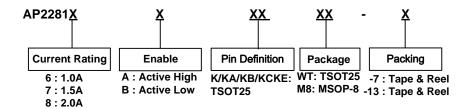
 T_A = Ambient temperature °C $R_{\theta JA}$ = Thermal resistance P_D = Total power dissipation

Board Layout Instruction

To minimize the effects of parasitic inductance, place input and output capacitors (1μ F and 0.1μ F+ 100μ F respectively) close and next to the device's pins. For the best performance, all trace lengths should be kept as short as possible and the input and output PCB traces should be as wide as possible. Use a ground plane to enhance the power dissipation capability of the device. For TOS25 Type KB and MSOP-8, it is recommended to connect all IN pins together and all OUT pins together to improve overall resistance value.



Ordering Information



Dant Neurolean	Package Code Package		7" and 13" Tape and Reel		
Part Number	Package Code	Package	Quantity	Part Number Suffix	
AP22816AKWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816BKWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816AKAWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816BKAWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816AKBWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816BKBWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816AKCWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816BKCWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816AKEWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22816BKEWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817AKAWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817BKAWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817AKBWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817BKBWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817AKCWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817BKCWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817AKEWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22817BKEWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818AKWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818BKWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818AKAWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818BKAWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818AKBWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818BKBWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818AKCWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818BKCWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818AKEWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818BKEWT-7	WT	TSOT25	3000/Tape & Reel	-7	
AP22818AM8-13	M8	MSOP-8	2500/Tape & Reel	-13	
AP22818BM8-13	M8	MSOP-8	2500/Tape & Reel	-13	



Marking Information

(1) TSOT25

(Top View)

5 4 XXX Y W X 1 2 3

XXX: Identification Code

Y : Year 0 to 9

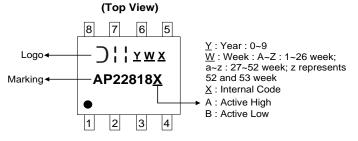
 \underline{W} : Week: A to Z: 1 to 26 week;

a to z : 27 to 52 week; z represents

52 and 53 week \underline{X} : Internal Code

Part Number	Package	Identification Code
AP22816AKWT-7	TSOT25	F2A
AP22816BKWT-7	TSOT25	F2B
AP22816AKAWT-7	TSOT25	F2C
AP22816BKAWT-7	TSOT25	F2D
AP22816AKBWT-7	TSOT25	F2E
AP22816BKBWT-7	TSOT25	F2F
AP22816AKCWT-7	TSOT25	F2G
AP22816BKCWT-7	TSOT25	F2H
AP22816AKEWT-7	TSOT25	F2J
AP22816BKEWT-7	TSOT25	F2K
AP22817AKAWT-7	TSOT25	F2M
AP22817BKAWT-7	TSOT25	F2N
AP22817AKBWT-7	TSOT25	F2P
AP22817BKBWT-7	TSOT25	F2R
AP22817AKCWT-7	TSOT25	F2S
AP22817BKCWT-7	TSOT25	F2T
AP22817AKEWT-7	TSOT25	F2U
AP22817BKEWT-7	TSOT25	F2V
AP22818AKWT-7	TSOT25	F2W
AP22818BKWT-7	TSOT25	F2X
AP22818AKAWT-7	TSOT25	F2Y
AP22818BKAWT-7	TSOT25	F2Z
AP22818AKBWT-7	TSOT25	F22
AP22818BKBWT-7	TSOT25	F23
AP22818AKCWT-7	TSOT25	F24
AP22818BKCWT-7	TSOT25	F25
AP22818AKEWT-7	TSOT25	F26
AP22818BKEWT-7	TSOT25	F27

(2) MSOP-8



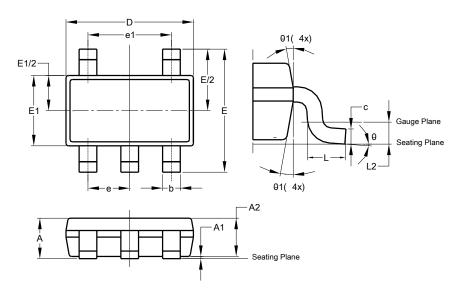
Part Number	Package	Identification Code
AP22818AM8-13	MSOP-8	AP22818A
AP22818BM8-13	MSOP-8	AP22818B



Package Outline Dimensions

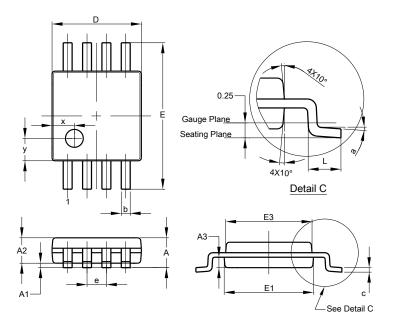
Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT25



	TSOT25			
Dim	Min	Max	Тур	
Α	-	1.00	-	
A1	0.01	0.10	-	
A2	0.84	0.90	-	
b	0.30	0.45	-	
С	0.12	0.20	-	
D	2.80	3.00	2.90	
Е	2.70	2.90	2.80	
E1	1.50	1.70	1.60	
е	0.95 BSC			
e1	,	1.90 BS	O	
L	0.30	0.50		
L2	0.25 BSC			
θ	0°	8°	4°	
θ1	4°	12°	-	
All [All Dimensions in mm			

MSOP-8



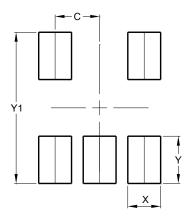
	MSOP-8			
Dim	Min	Max	Тур	
Α	-	1.10	-	
A1	0.05	0.15	0.10	
A2	0.75	0.95	0.86	
A3	0.29	0.49	0.39	
b	0.22	0.38	0.30	
С	0.08	0.23	0.15	
D	2.90	3.10	3.00	
Е	4.70	5.10	4.90	
E1	2.90	3.10	3.00	
E3	2.85	3.05	2.95	
е	-	-	0.65	
L	0.40	0.80	0.60	
а	0°	8°	4°	
х	-	-	0.750	
у	-	-	0.750	
All Dimensions in mm				



Suggested Pad Layout

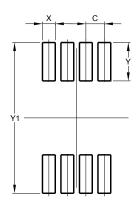
Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT25



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199

MSOP-8



Dimensions	Value (in mm)	
C	0.650	
Х	0.450	
Υ	1.350	
Y1	5.300	



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